

1. Scope

The present specifications shall apply to an SJPZ-N18.

2. Outline

Type	Silicon Diode
Structure	Resin Molded
Applications	Over Voltage Absorption

3. Flammability

UL94V-0 (Equivalent)

4. Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Permissible Power loss	P	W	2	Refer to Derating of 6
2	Transient Peak Reverse Power	P_{RSM}	W	500	Single Square Wave
3	Junction Temperature	T_j	°C	-55~+150	—
4	Storage Temperature	T_{stg}	°C	-55~+150	—

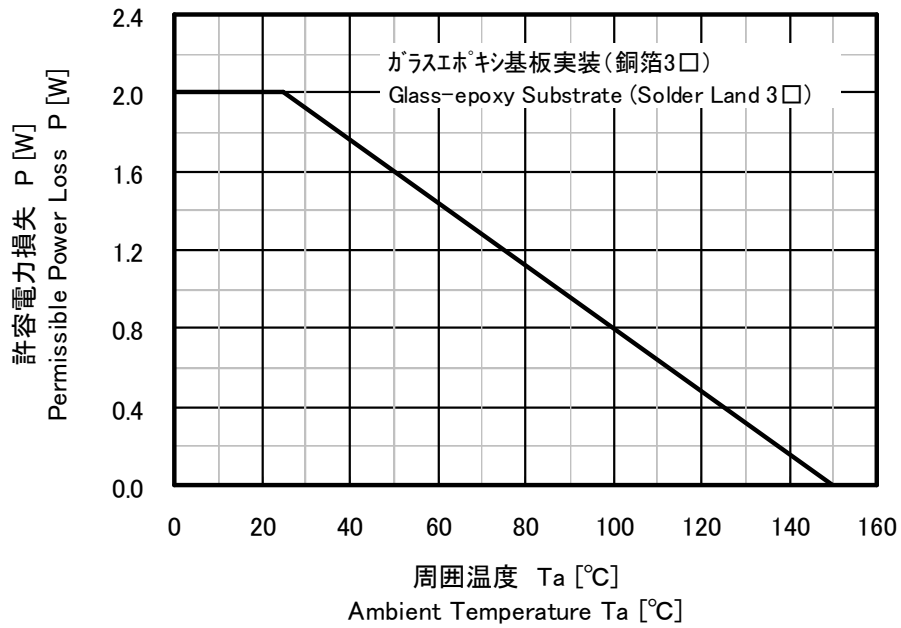
5. Electrical characteristics($T_a=25^{\circ}\text{C}$, unless otherwise specified)

No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	1.2 max.	$I_F=2\text{A}$
2	Reverse Breakdown Voltage	V_Z	V	16.8 ~ 19.1	$I_Z=1\text{mA}$
3	Reverse Leakage Current	I_R	uA	1 max.	$V_R=13\text{V}$
4	Temperature Coefficient Breakdown Voltage	γ_z	mV/°C	13 typ.	$I_Z=1\text{mA}$
5	Equivalent Resistance of Breakdown Region	R_z	Ω	2 typ.	$I_z=10\text{mA} \sim 20\text{mA}$

6. Derating

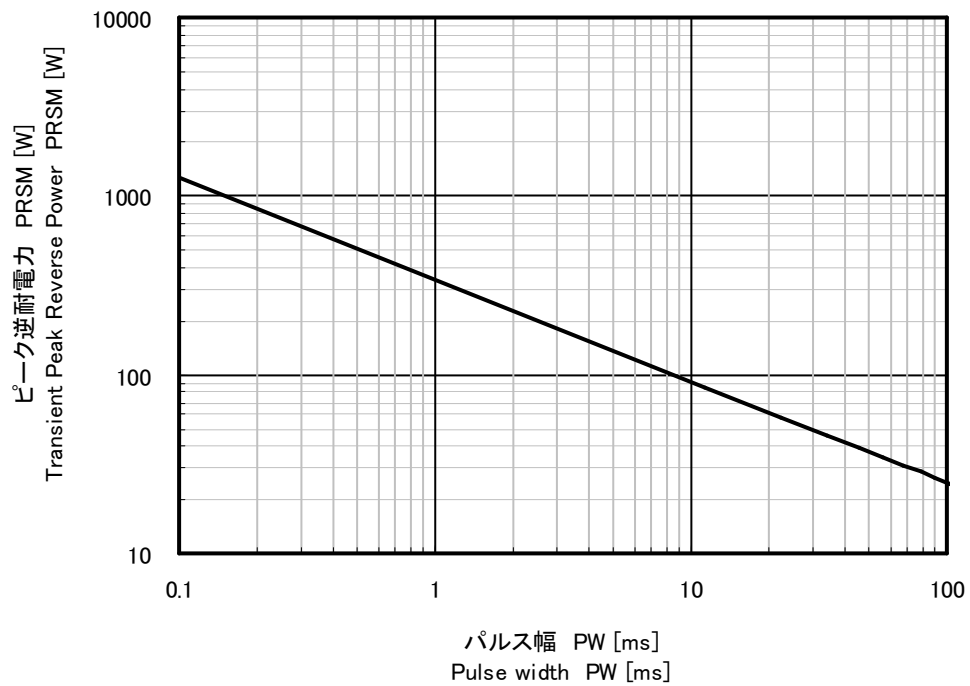
Permissible Power Loss

周囲温度－許容電力損失
Permissible Power Loss - Ambient Temperature



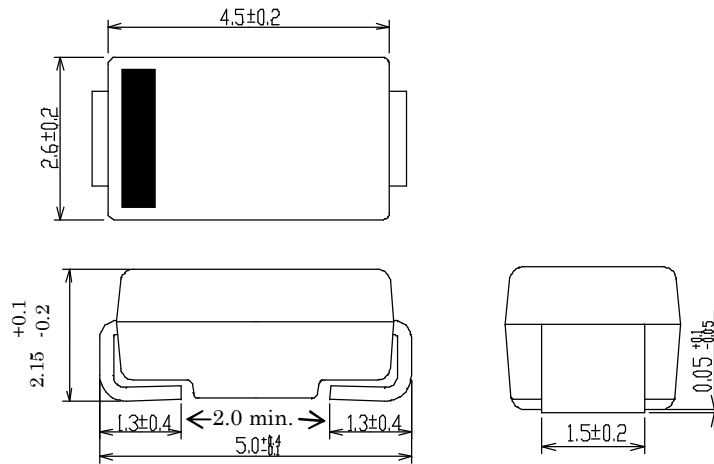
7. Transient Peak Reverse Power Rating

ピーク逆耐電力－パルス幅
Transient Peak Reverse Power - Pulse width



8. Package information

8-1 Package type, physical dimensions

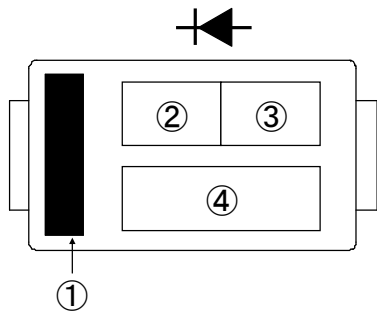


Dimensions in mm

8-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3 Marking



1 Polarity marking (Cathode band)

2 Type number

SJPZ-N as abbreviated of ZN.

Vz Class number

18V as abbreviated of 18.

3 Lot number

Example) 9615

9: Last number of Year

6: Month from 1 to 9 for Jan. to Sep. O for Oct. , N for Nov. , D for Dec.
15: Day.

